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DMPH6250SQ

60V 175°C P-CHANNEL ENHANCEMENT MODE MOSFET

Rated to +175°C-Ideal for High Ambient Temperature

Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2) Halogen and Antimony Free. "Green" Device (Note 3) Qualified to AEC-Q101 Standards for High Reliability

Case Material: Molded Plastic, "Green" Molding Compound.

Terminals: Finish-Matte Tin Annealed over Copper Leadframe.

UL Flammability Classification Rating 94V-0 Moisture Sensitivity: Level 1 per J-STD-020

Solderable per MIL-STD-202, Method 208 @3

Terminals Connections: See Diagram Below

Weight: 0.008 grams (Approximate)

Features and Benefits

PPAP Capable (Note 4)

Mechanical Data
Case: SOT23

Environments Low On-Resistance Low Input Capacitance Fast Switching Speed Low Input/Output Leakage

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	155mΩ @ V _{GS} = -10V	-2.4A
-60V	240mΩ @ V _{GS} = -4.5V	-1.9A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

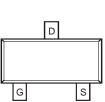
- Battery Charging
- Power Management Functions
- DC-DC Converters
- Load Switch



Top View

G

Internal Schematic



Top View

Ordering Information (Note 5)

Part Number	Case	Packaging
DMPH6250SQ-7	SOT23	3000/Tape & Reel
DMPH6250SQ-13	SOT23	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Π	
H62	ΥM

H62 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Key												
Year	2017		2018	2019		2020	2021		2022	2023		2024
Code	E		F	G		Н			J	K		L
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

DMPH6250SQ Document number: DS40279 Rev. 3 - 2



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	-60	V	
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Current (Note 7) V_{GS} = -10V	Steady State	T _A = +25°C T _A = +100°C	ID	-2.4 -1.5	А
Pulsed Drain Current (380µs Pulse, Duty Cycle =	= 1%)	I _{DM}	-13	A	
Maximum Continuous Body Diode Forward Curre	ent (Note 7	Is	-1.6	A	
Pulsed Body Diode Forward Current (380µs Puls	se, Duty C	ycle = 1%)	I _{SM}	-13	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	PD	0.92	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 6)	R _{ÐJA}	165	°C/W
Power Dissipation (Note 7)	PD	1.62	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 7)	R _{ÐJA}	93.1	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +175	°C

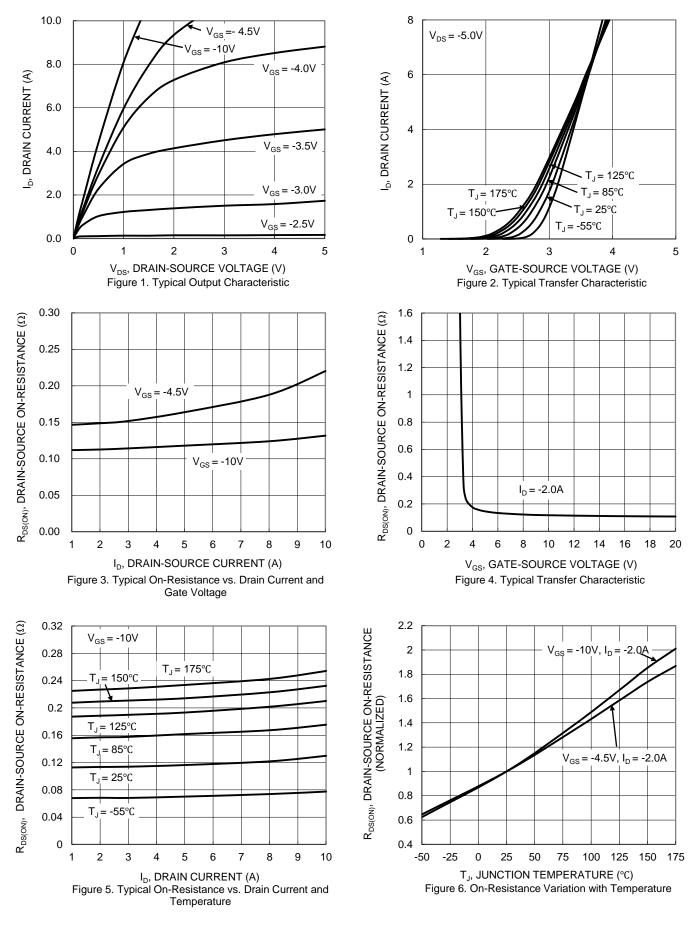
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

			-			
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)				1	1	
Drain-Source Breakdown Voltage	BV _{DSS}	-60	—	—	V	$V_{GS} = 0V, I_D = -250 \mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}		—	-1.0	μA	$V_{DS} = -60V, V_{GS} = 0V$
Gate-Source Leakage	IGSS		—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-1.0	-1.9	-3.0	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
Static Drain-Source On-Resistance	P	—	112	155	mΩ	$V_{GS} = -10V, I_D = -2A$
	R _{DS(ON)}	—	149	240	11152	$V_{GS} = -4.5V, I_D = -2A$
Diode Forward Voltage	V _{SD}	_	-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	—	512	—	pF	
Output Capacitance	Coss	—	31.3	—	pF	$V_{DS} = -30V, V_{GS} = 0V,$ - f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	—	23.2	_	pF	1 = 1.00012
Gate Resistance	Rg	—	11.9	—	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = -4.5V)	Qg	—	4.0	—	nC	
Total Gate Charge (V _{GS} = -10V)	Qg	_	8.3	—	nC	Vps = -30V. lp = -2A
Gate-Source Charge	Q _{gs}	—	1.2	—	nC	$v_{DS} = -30v, ID = -2A$
Gate-Drain Charge	Q _{gd}	_	1.7	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	12.5	—	ns	
Turn-On Rise Time	t _R	_	13.4	—	ns	$V_{DD} = -30V, V_{GS} = -10V,$
Turn-Off Delay Time	t _{D(OFF)}		96.0	_	ns	$I_{D} = -1.0A, R_{G} = 50\Omega$
Turn-Off Fall Time	tF	_	39.1	—	ns	
Body Diode Reverse Recovery Time	t _{RR}	_	9.6	_	ns	I _F = -1A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q _{RR}	_	3.1	_	nC	I _F = -1A, di/dt = 100A/µs

 Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing. Notes:

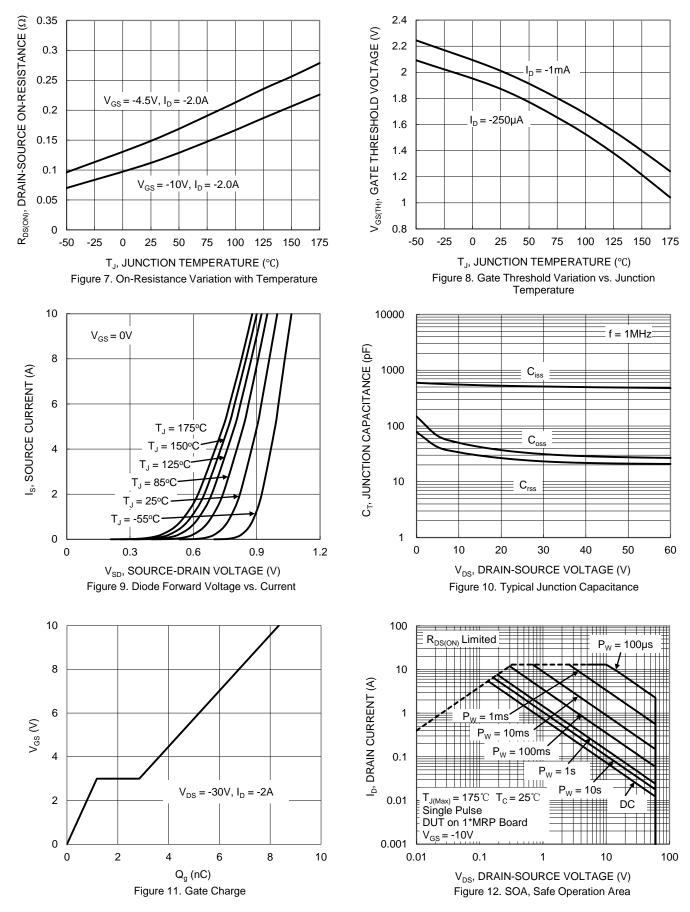


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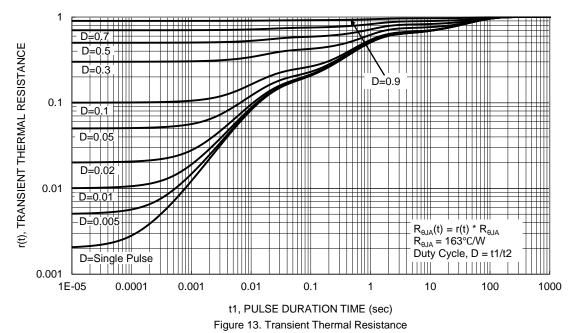




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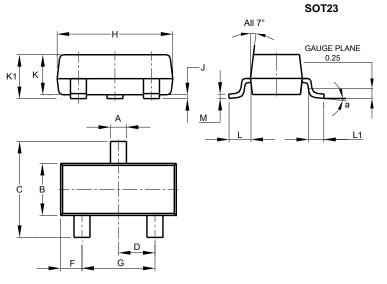






Package Outline Dimensions

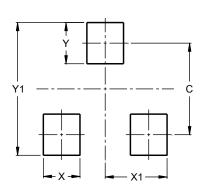
Please see http://www.diodes.com/package-outlines.html for the latest version.



	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
ĸ	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	0°	8°						
All	All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9

w.diodes.com/package-outlines.htm



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